

Electronic Information Disclosure Statement

DIFFUSED EXTRINSIC BASE AND METHOD FOR FABRICATION

JC474 U.S. PTO
10/064476



Application:

Confirmation:

Applicant(s): Marc Cantell

Docket Number: BUR920010036

Group Art Unit:

Examiner:

search string: (5761080 or 5629556 or 5593905 or 5439833 or 5268314 or 5117271 or 4860085 or 4495512 or 4252581 or 3904450).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
01/4	P01	5761080	1998-06-02		DeCamp, et al.	364	490
1	P02	5629556	1997-05-13		Johnson	257	592
1	P03	5593905	1997-01-14		Johnson, et al.	437	31
1	P04	5439833	1995-08-08		Hebert, et al.	437	31
1	P05	5268314	1993-12-07		Connor	437	31
1	P06	5117271	1992-05-26		Comfort, et al.	357	34
1	P07	4860085	1989-08-22		Feygenson	357	59
1	P08	4495512	1985-01-22		Isaac, et al.	357	34

<i>MA</i>	P09	4252581	1981-02-24		Anantha, et al.	148	175
<i>MA</i>	P10	3904450	1975-09-09		Evans, et al.	148	175

Remarks

(Remarks are not for responding to an office action.)

IBM Technical Disclosure Bulletin, Vol. 26, No. 2, July 1983, "Transistor Collector Doping for Reduced Capacitance", W.P. Dumke, p. 492. IBM Technical Disclosure Bulletin, Vol. 25, No. 4, September 1982, "Using a Doubly Implanted Polysilicon Layer for Forming Base and Emitter Regions", C.G. Jambotkar, pp. 1987-1989. IBM Technical Disclosure Bulletin, Vol. 24, No. 7A, December 1981, "Polycide Bipolar Transistor Process", F. Barson, et al., pp. 3424-3426.

Signature

Examiner Name	Date
<i>Kang, Donghee</i>	<i>04/14/03</i>